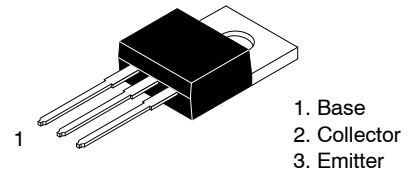


NPN Silicon Transistor

KSC5027

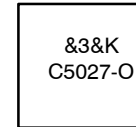
High Voltage and High Reliability

- High Speed Switching
- Wide SOA



TO-220-3LD
CASE 340AT

MARKING DIAGRAM



- &3 = Date Code (Year & Week)
- &K = Lot Run Traceability Code
- C5027 = Specific Device Code
- O = h_{FE} Grade

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	3	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	1.5	A
P_C	Collector Dissipation ($T_C = 25^\circ\text{C}$)	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

Device	Package	Shipping
KSC5027OTU	TO-220-3LD (Pb-Free, Halide Free)	1000 Units / Tube

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 1\text{ mA}, I_E = 0$	1100	-	-	V
BV_{CBO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{ mA}, I_B = 0$	800	-	-	V
BV_{CBO}	Emitter-Base Breakdown Voltage	$I_E = 1\text{ mA}, I_C = 0$	7	-	-	V
$V_{CEX(sus)1}$	Collector-Emitter Sustaining Voltage	$I_C = 1.5\text{ A}, I_{B1} = -I_{B2} = 0.3\text{ A}, L = 2\text{ mH}, \text{Clamped}$	800	-	-	V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 800\text{ V}, I_E = 0$	-	-	10	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5\text{ V}, I_C = 0$	-	-	10	μA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 0.2\text{ A}$ $V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	10 8	-	40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1.5\text{ A}, I_B = 0.3\text{ A}$	-	-	2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1.5\text{ A}, I_B = 0.3\text{ A}$	-	-	1.5	V
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	-	60	-	μs
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{ V}, I_C = 0.2\text{ A}$	-	15	-	MHz
t_{ON}	Turn On Time	$V_{CC} = 400\text{ V}, I_C = 5\text{ A}, I_{B1} = -2.5, I_{B2} = 2\text{ A}, R_L = 200\ \Omega$	-	-	0.5	μs
t_{STG}	Storage Time		-	-	3	μs
t_F	Fall Time		-	-	0.3	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} Classification

Classification	N	R	O
h_{FE1}	10 ~ 20	15 ~ 30	20 ~ 40

TYPICAL CHARACTERISTICS

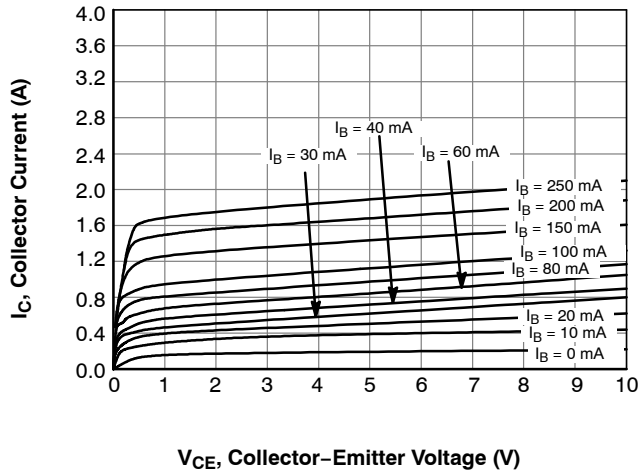


Figure 1. Static Characteristic

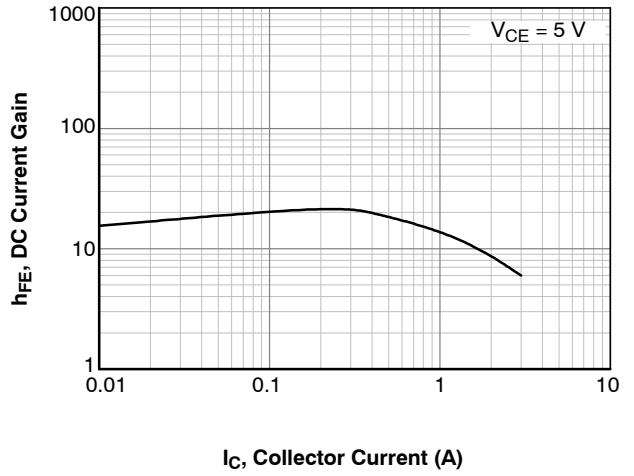


Figure 2. DC Current Gain

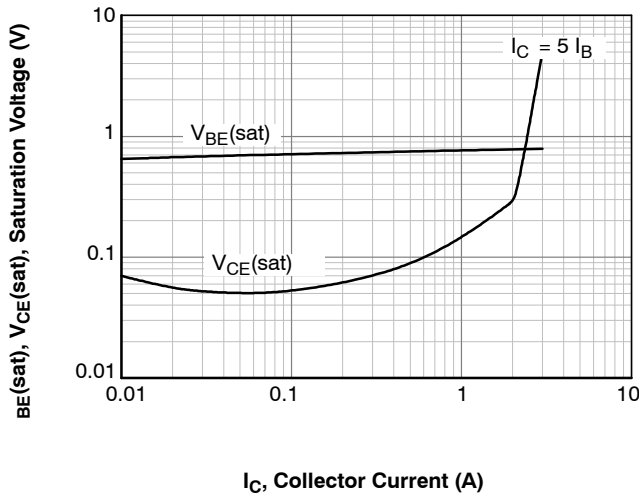


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

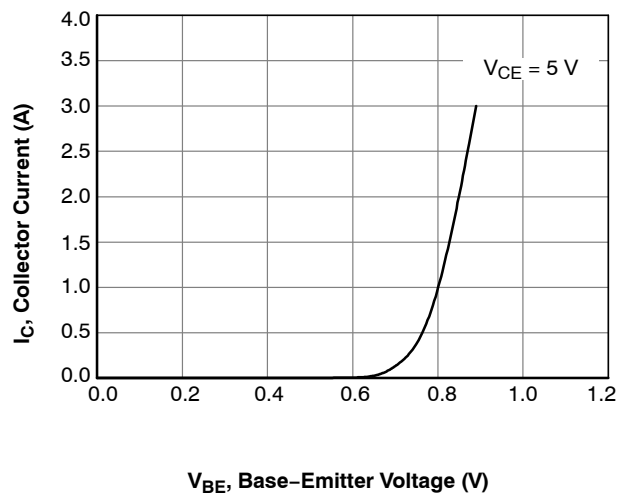


Figure 4. Base-Emitter On Voltage

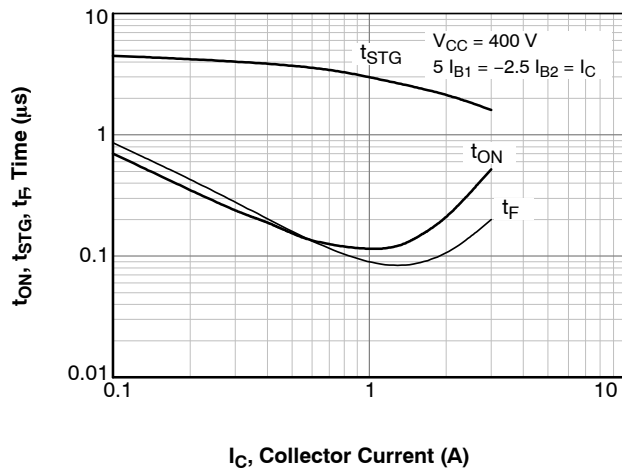


Figure 5. Switching Time

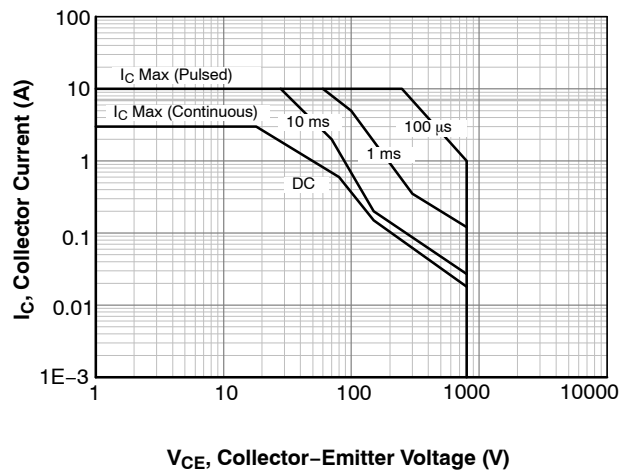
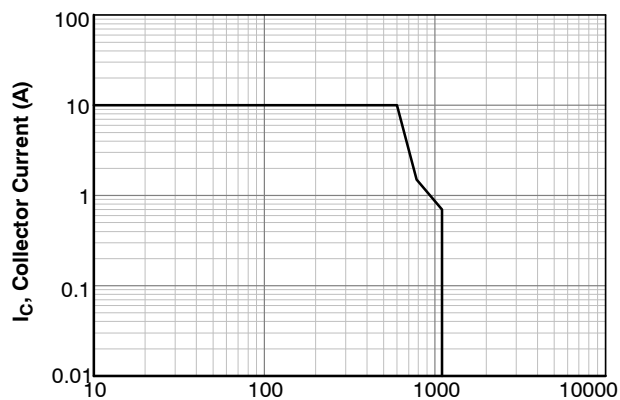


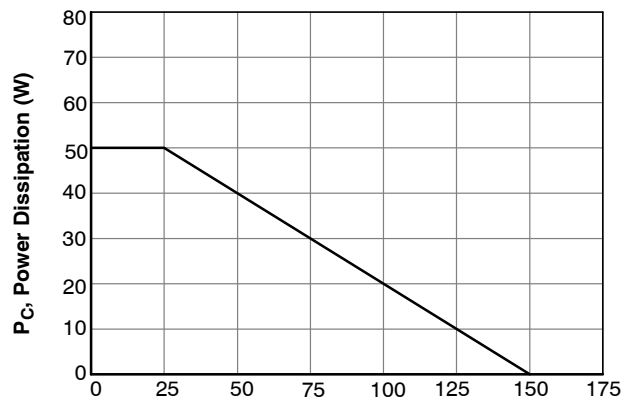
Figure 6. Safe Operating Area

TYPICAL CHARACTERISTICS (Continued)



V_{CE} , Collector-Emitter Voltage (V)

Figure 7. Reverse Bias Operating Areas



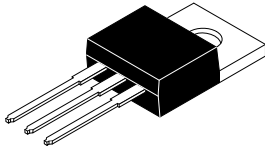
T_C , Case Temperature ($^{\circ}C$)

Figure 8. Power Derating

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

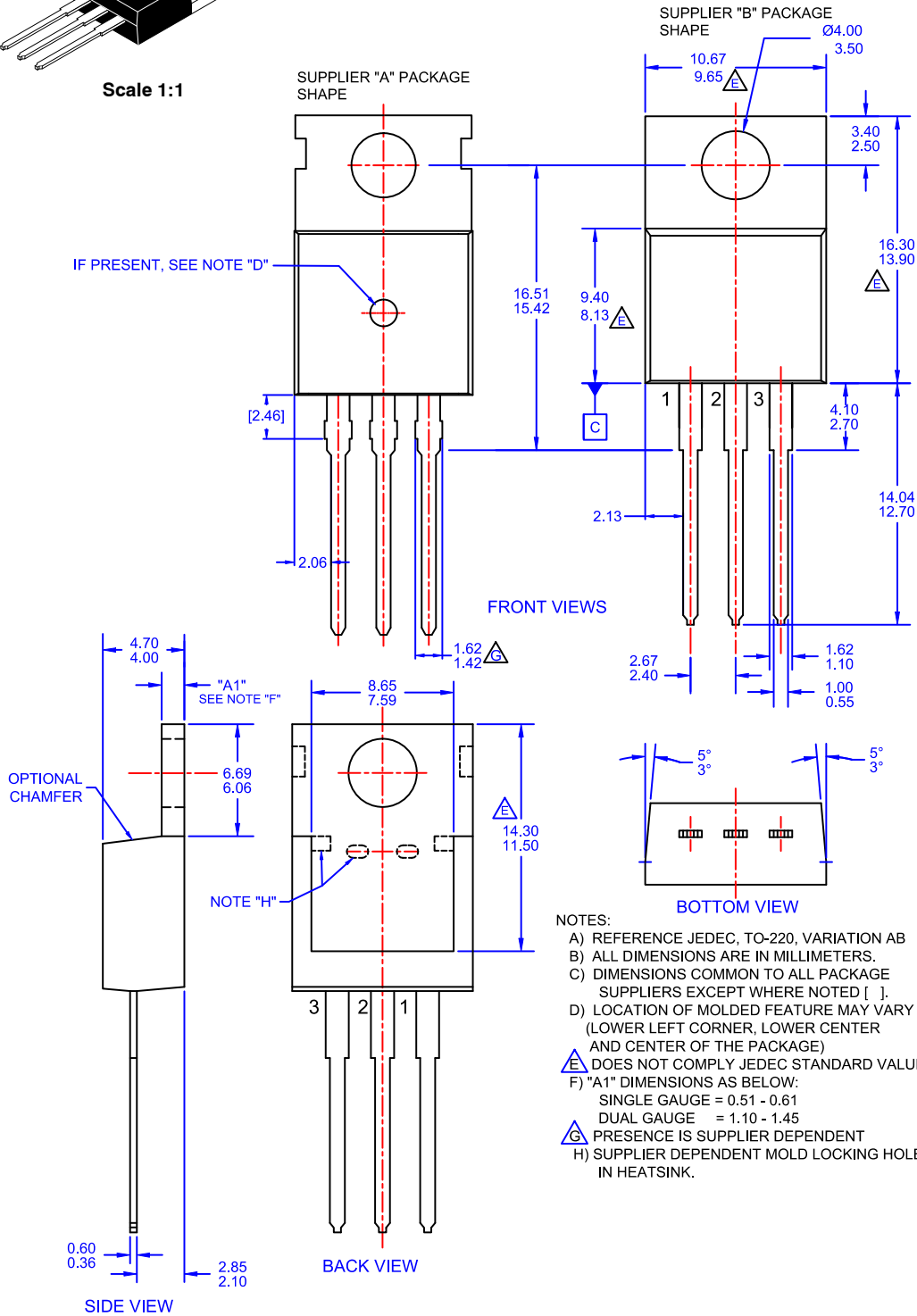
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Scale 1:1

TO-220-3LD CASE 340AT ISSUE A

DATE 03 OCT 2017



- NOTES:
- A) REFERENCE JEDEC, TO-220, VARIATION AB
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [].
 - D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
 - E) DOES NOT COMPLY JEDEC STANDARD VALUE.
 - F) "A1" DIMENSIONS AS BELOW:
 SINGLE GAUGE = 0.51 - 0.61
 DUAL GAUGE = 1.10 - 1.45
 - G) PRESENCE IS SUPPLIER DEPENDENT
 - H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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